

Title (en)

PROCESS FOR PREPARING POLYCRYSTALLINE SILICON

Title (de)

VERFAHREN ZUR HERSTELLUNG VON POLYKRISTALLINEM SILICIUM

Title (fr)

PROCÉDÉ DE PRODUCTION DE SILICIUM POLYCRISTALLIN

Publication

EP 3649078 A1 20200513 (DE)

Application

EP 16823183 A 20161214

Priority

EP 2016080900 W 20161214

Abstract (en)

[origin: WO2018108258A1] The invention relates to a method for producing polycrystalline silicon granulate in a fluidized bed reactor. The method comprises a fluidization of silicon seed particles by means of a fluidizing gas in a fluidized bed, which is heated by a heating device, wherein elemental silicon is deposited by pyrolysis on the silicon seed particles by the addition of a reaction gas containing hydrogen and silane and/or halosilane to form the polycrystalline silicon granulate. In a continuous process, waste gas is discharged from the fluidized bed reactor and hydrogen recovered from said waste gas is again supplied to the fluidized bed reactor as a circulating gas. The circulating gas has a nitrogen content of less than 1000 ppmv. The invention further relates to polycrystalline silicon granulate having a nitrogen content of less than 2 ppba.

IPC 8 full level

C01B 33/02 (2006.01); **C01B 33/03** (2006.01)

CPC (source: EP KR US)

C01B 33/02 (2013.01 - EP); **C01B 33/03** (2013.01 - EP KR US)

Citation (search report)

See references of WO 2018108258A1

Designated contracting state (EPC)

AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

DOCDB simple family (publication)

WO 2018108258 A1 20180621; WO 2018108258 A8 20190516; CA 3045350 A1 20180621; CN 110049948 A 20190723;
CN 110049948 B 20221011; EP 3649078 A1 20200513; JP 2020502027 A 20200123; JP 6977041 B2 20211208; KR 102220841 B1 20210226;
KR 20190074317 A 20190627; MY 194441 A 20221130; US 11440803 B2 20220913; US 2020131043 A1 20200430

DOCDB simple family (application)

EP 2016080900 W 20161214; CA 3045350 A 20161214; CN 201680091468 A 20161214; EP 16823183 A 20161214;
JP 2019531720 A 20161214; KR 20197016561 A 20161214; MY PI2019002858 A 20161214; US 201616469628 A 20161214